

isc Silicon PNP Power Transistor

2SB962-Z

DESCRIPTION

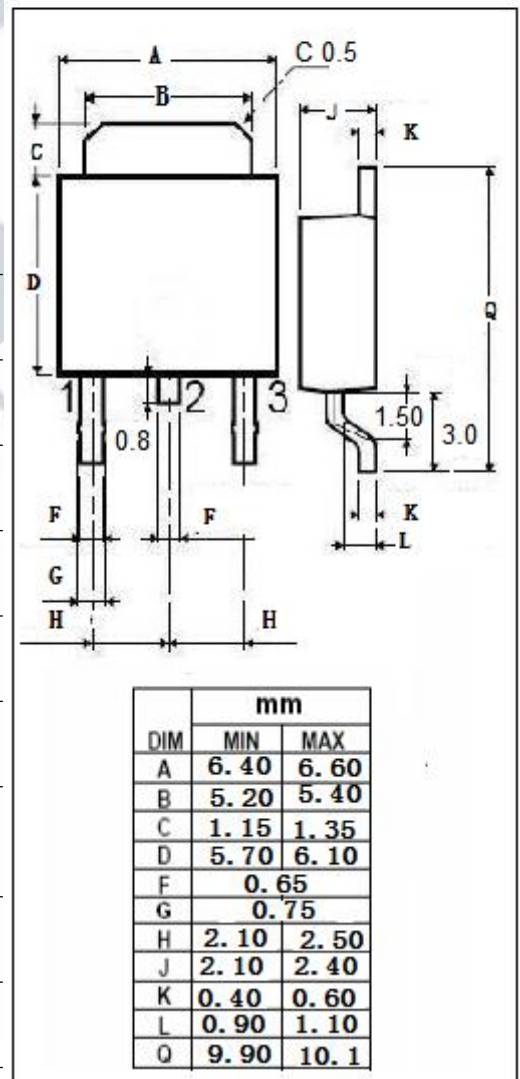
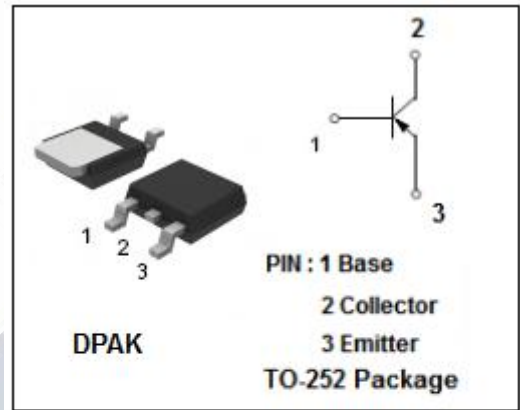
- Low $V_{CE(sat)} = -0.3V$ TYP
- PNP silicon epitaxial transistor
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- The 2SB962-Z is designed for Audio frequency amplifier and switching ,especially in hybrid integrated circuits

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
I_{CP}	Collector Current-Pulse	-6	A
P_C	Total Power Dissipation @ $T_a=25^{\circ}C$	2.0	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SB962-Z****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CE(sat)}^{NOTE}$	Collector-Emitter Saturation Voltage	$I_C = -2.0A; I_B = -200mA$			-0.5	V
$V_{BE(sat)}^{NOTE}$	Base-Emitter Saturation Voltage	$I_C = -2.0A; I_B = -200mA$			-2.0	V
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -3V; I_C = 0$			-1.0	μA
I_{CBO}	Collector Cutoff Current	$V_{CB} = -30V; I_E = 0$			-10	μA
h_{FE1}^{NOTE}	DC Current Gain	$I_C = -1A; V_{CE} = -2V$	60		400	
h_{FE2}^{NOTE}	DC Current Gain	$I_C = -20mA; V_{CE} = -2V$	30			
fT	Transition frequency	$V_{CE} = -5V, I_C = -100mA$		80		MHz
Cob	Collector output capacitance	$V_{CB} = -10V, I_E = 0, f = 1MHz$		55		pF

NOTE: Pulse test $PW \leq 350\mu s$, duty cycle $\leq 2\%$ ◆ h_{FE1} Classifications

R	Q	P	E
60-120	100-200	160-320	200-400